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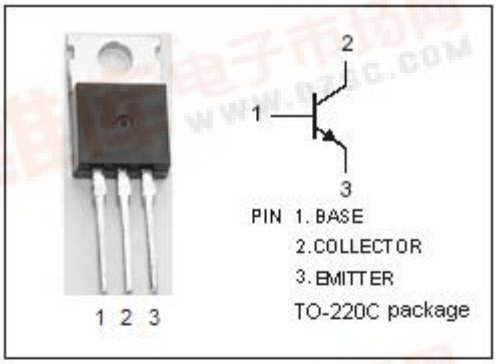
isc Silicon NPN Power Transistor 2N6833

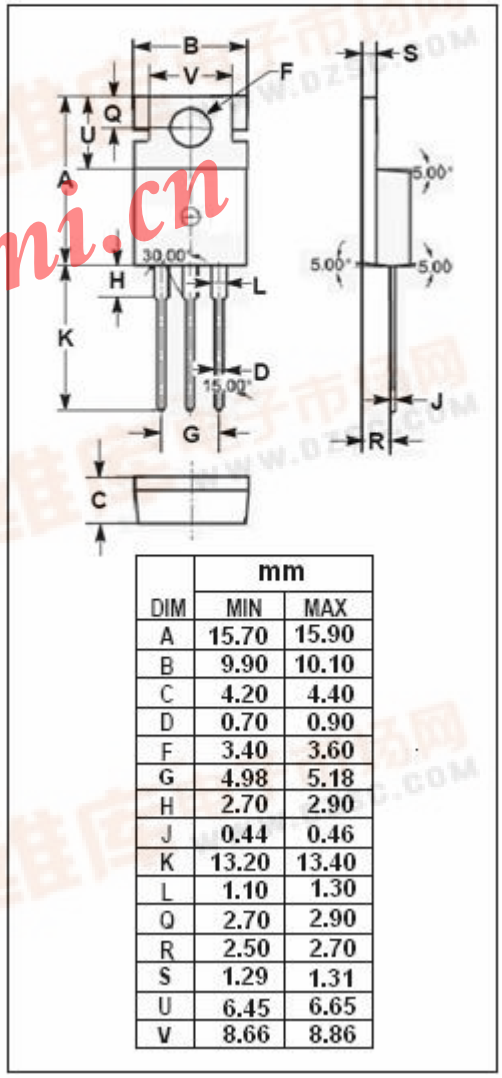
DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = 450V(Min)
- High Switching Speed



APPLICATIONS

- Designed for high-voltage ,high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line operated switch-mode applications.
  Typical applications:
- Switching regulators
- Inverters
- Solenoid and relay drivers
- Motor controls
- Deflection circuits



DIM	mm MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage	850	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current-Continuous	4	A
I_{BM}	Base Current-Peak	8	A
P_C	Collector Power Dissipation@T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.56	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C=100mA ; I_B=0	450			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 1.5A; I_B= 0.15A			1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 0.4A I_C= 3A; I_B= 0.4A,T_C=100℃			2.5 2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 3A; I_B= 0.4A I_C= 3A; I_B= 0.4A,T_C=100℃			1.5 1.5	V
I_{CEV}	Collector Cutoff Current	V_{CEV}= 850V;$V_{BE(off)}$= 1.5V V_{CEV}= 850V;$V_{BE(off)}$= 1.5V;T_C=100℃			0.25 1.5	mA
I_{CER}	Collector Cutoff Current	V_{CE}= 850V; R_{BE}= 50Ω ,T_C= 100℃			2.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6.0V; I_C=0			1.0	mA
h_{FE-1}	DC Current Gain	I_C= 3A ; V_{CE}= 5V	7.5		30	
h_{FE-2}	DC Current Gain	I_C= 5A ; V_{CE}= 5V	5			
f_T	Current Gain-Bandwidth Product	I_C= 0.25A ;V_{CE}= 10V; f_{test}=10MHz	15		75	MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f_{test}=1.0kHz	20		200	pF

Switching times;Resistive Load

t_d	Delay Time	I_C= 3A , V_{CC}= 250V; I_{B1}= 0.4A; I_{B2}= -0.8A; P_W= 30μs; R_{B2}= 8Ω Duty Cycle≤2.0%		0.03	0.1	μs
t_r	Rise Time			0.1	0.3	μs
t_s	Storage Time			1.0	3.0	μs
t_f	Fall Time			0.06	0.3	μs

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